Vishay Siliconix

# N-Channel 25 V (D-S) MOSFET

## **DESCRIPTION**

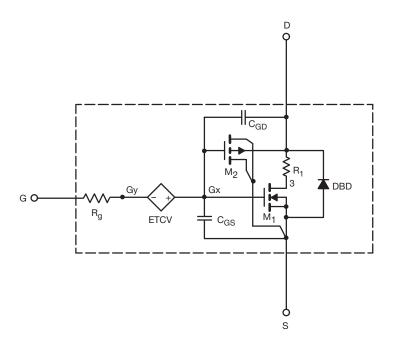
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over -55 °C to +125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{\rm gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### **CHARACTERISTICS**

- N-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- · Apply for both linear and switching application
- Accurate over -55 °C to +125 °C temperature range
- · Model the gate charge

### SUBCIRCUIT MODEL SCHEMATIC



## Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.





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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.6	-	V
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A	0.00064	0.00063	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	0.00098	0.00093	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A	129	89	S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 5 A	0.72	0.71	V
Dynamic <sup>b</sup>					
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	7600	7570	pF
Output Capacitance	Coss		2120	2130	
Reverse Transfer Capacitance	C <sub>rss</sub>		475	502	
Total Gate Charge	Qg	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	104	102	nC
		$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 10 \text{ A}$	48	45.5	
Gate-Source Charge	Q <sub>gs</sub>		17	17	
Gate-Drain Charge	Q <sub>gd</sub>		8.3	8.3	

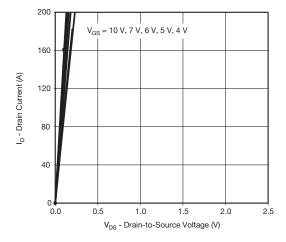
#### Notes

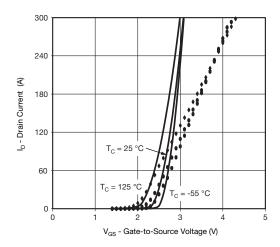
- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing

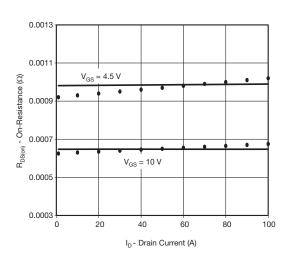
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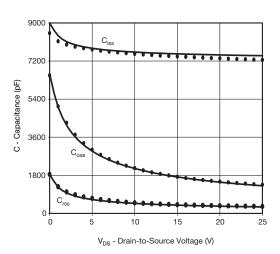
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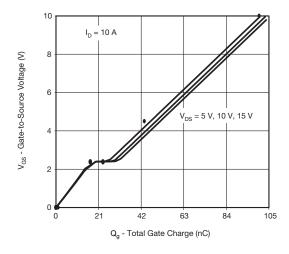
## **COMPARISON OF MODEL WITH MEASURED DATA** ( $T_J = 25~^{\circ}C$ , unless otherwise noted)

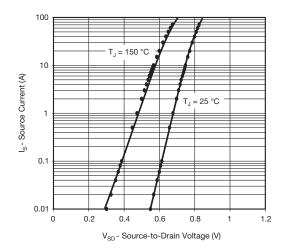












## Note

· Dots and squares represent measured data.

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